YJ Planar Schottky Barrier Diode Die Specification

150V 30A, 122mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB122H150AS-280A

Main Products Characterstics

- Average forward current: IF(AV) = 30
- Maximum operating junction temperature: Tj = 175 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

Symbol

I_F = 15A

Pulse Test: tp = 300 μs, δ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area

Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.